



S/N 09/945,535

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Applicant: Kie Y. Ahn et al.

Examiner: David B. 2002

Serial No.: 09/945,535

Group Art Unit: 2813

Filed: August 30, 2001

TECHNOLOGY CENTER 2800
Docket: 1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO₂

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on June 5, 2002. Please amend the above-identified patent application as follows.

IN THE DRAWINGS

The Examiner has stated that, "Figures and 2A-2C should be designated by a legend such as – Prior Art– because only that which is old is illustrated. See MPEP 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office Action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance."

Enclosed is a copy of Figures 1 and 2A-2C of the drawings showing the following proposed amendments in red ink. Pursuant to the Examiner's suggestion, Figures 1 and 2A-2C have been labeled "prior art."

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of previously pending claims 1, 9, 14, 22, 30, and 51. The specific amendments to individual claims are detailed in the following marked up set of claims.

1. (Amended) A method of forming a gate oxide on a transistor body region, comprising: evaporation depositing a metal layer on the body region using a substantially thermal process, the metal being chosen from the group IVB elements of the periodic table; and oxidizing the metal layer to form a metal oxide layer on the body region.